

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (currently amended): For heating operations in semiconductor manufacturing equipment, a ceramic susceptor ~~having a resistive heating element on a surface of or inside~~ comprising:

a ceramic substrate[[,]] defining a wafer-support side and being processed so that
when the susceptor is not heating, along the susceptor thickness ~~the ceramic susceptor for~~
~~semiconductor manufacturing equipment characterized in that~~ the difference between a the
maximum outer diameter and the minimum outer diameter in an arbitrary plane is 0.8% or
less of the average outer diameter along the susceptor wafer-support side ~~when not heating;~~
and

a resistive heating element provided either on a surface of or inside said ceramic
substrate.

Claim 2 (currently amended): A ceramic susceptor for semiconductor manufacturing equipment as set forth in claim 1, ~~characterized in that~~ wherein the ceramic substrate is made of at least one ceramic selected from aluminum nitride, silicon nitride, aluminum oxynitride, and silicon carbide..

Claim 3 (currently amended): A ceramic susceptor for semiconductor manufacturing equipment as set forth in claim 1 ~~or 2, characterized in that,~~ wherein the resistive heating

element is made from at least one metal selected from tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

Claim 4 (currently amended): A ceramic susceptor for semiconductor manufacturing equipment as set forth in ~~any of claims 1 through 3, characterized in that~~ claim 1, wherein a plasma electrode is further disposed on a surface of or inside the ceramic substrate.

Claim 5 (new): A ceramic susceptor for semiconductor manufacturing equipment as set forth in claim 2, wherein the resistive heating element is made from at least one metal selected from tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

Claim 6 (new): A ceramic susceptor for semiconductor manufacturing equipment as set forth in claim 2, wherein a plasma electrode is further disposed on a surface of or inside the ceramic substrate.

Claim 7 (new): A ceramic susceptor for semiconductor manufacturing equipment as set forth in claim 3, wherein a plasma electrode is further disposed on a surface of or inside the ceramic substrate.

Claim 8 (new): A ceramic susceptor for semiconductor manufacturing equipment as set forth in claim 5, wherein a plasma electrode is further disposed on a surface of or inside the ceramic substrate.